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## FDB031N08 N 沟道 PowerTrench<sup>®</sup> MOSFET 75 V, 235 A, 3.1 mΩ

### 特性

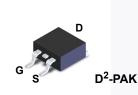
- $R_{DS(on)}$  = 2.4 m $\Omega$  (Typ.)@V<sub>GS</sub> = 10 V, I<sub>D</sub> = 75 A
- 快速开关速度
- 低栅极电荷
- 高性能沟道技术可实现极低的 R<sub>DS(on)</sub>
- 高功率和高电流处理能力
- ・ 符合 RoHS 标准

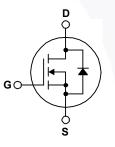
### 说明

此 N 沟道 MOSFET 采用飞兆半导体先进的 PowerTrench<sup>®</sup> 工艺 生产,这一先进工艺是专为最大限度地降低导通电阻并保持卓越 开关性能而定制的。

### 应用

- 用于 ATX/ 服务器 / 电信 PSU 的同步整流
- 电池保护电路
- 电机驱动和不间断电源





### MOSFET 最大额定值 TC = 25°C 除非另有说明。

| 符号                                |                              |      | 参数                              |        | FDB031N08  | 单位   |
|-----------------------------------|------------------------------|------|---------------------------------|--------|------------|------|
| V <sub>DSS</sub>                  | 漏极一源极电压                      |      |                                 |        | 75         | V    |
| V <sub>GSS</sub>                  | 栅极一源极电压                      |      |                                 |        | ±20        | V    |
|                                   | 漏极电流                         | - 连续 | 载(T <sub>C</sub> =25°C,硅片受限)    |        | 235        | Α    |
| ID                                |                              | - 连续 | 载(T <sub>C</sub> =100°C,硅片受限)   |        | 165        | Α    |
|                                   |                              | - 连续 | - 连续(T <sub>C</sub> =25°C,封装受限) |        | 120        | A    |
| ОМ                                | 漏极电流                         |      | - 脉冲                            | (说明 1) | 940        | А    |
| E <sub>AS</sub>                   | 单脉冲雪崩能量 (说明 2)               |      |                                 | (说明 2) | 1995       | mJ   |
| dv/dt                             | 二极管恢复 dv/dt 🛙                | 夆值   |                                 | (说明 3) | 5.5        | V/ns |
| P <sub>D</sub>                    |                              |      |                                 | 375    | W          |      |
|                                   | 功耗 - 降低至 25℃ 以上              |      |                                 |        | 2.5        | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | 工作和存储温度范围                    |      |                                 |        | -55 至 +175 | °C   |
| TL                                | 用于焊接的最大引线温度,距离外壳 1/8",持续 5 秒 |      |                                 |        | 300        | °C   |

#### 热性能

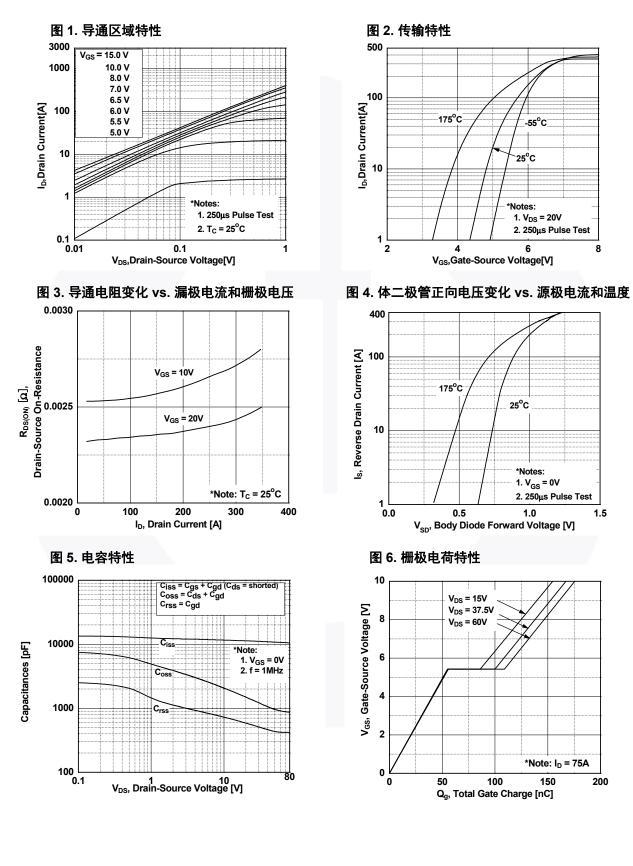
| 符号                    | 参数         | FDB031N08 | 单位   |
|-----------------------|------------|-----------|------|
| $R_{	extsf{	heta}JC}$ | 结至外壳热阻最大值。 | 0.4       | °C/W |
| $R_{	extsf{	heta}JA}$ | 结至环境热阻最大值。 | 62.5      | 0/11 |

2014年2月

| 器件组                                | 扁号                                       | 顶标                  | 封装 | 包装方法  | 卷尺寸                 |     | 带宽    | 数     |      |
|------------------------------------|--|---------------------|----|---|---------------------|-----|-------|-------|------|
|                                    |  | D <sup>2</sup> -PAK |    |   | 24 mm               |     | 800 个 |       |      |
|                                    |  |                     |    |   |                     |     |       |       |      |
| 电气特性                               | TC = 25°C                                | 除非另有说明。             |    |   |                     |     |       |       |      |
| 符号                                 |  | 参数                  |    | 测试条件  |                     | 最小值 | 典型值   | 最大值   | 单位   |
| 关断特性                               |  |                     |    |   |                     |     |       |       |      |
| BV <sub>DSS</sub>                  | 漏极—源                                     | 极击穿电压               |    | I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V  | $T_c = 25^{\circ}C$ | 75  | -     | -     | V    |
| $\Delta BV_{DSS}$                  |  |                     |    |   |                     | -   |       |       |      |
| $/\Delta T_J$                      |  | 山才屯止/皿皮尔效           |    | I <sub>D</sub> = 250 μA,温度参考 25°C   |                     |     | 0.05  | -     | V/°C |
|                                    | <b>雯</b> 娜扔由                             | 零栅极电压漏极电流           |    | $V_{DS}$ = 75 V, $V_{GS}$ = 0 V   |                     | -   | -     | 1     | ıιΔ  |
| DSS                                | 令伽似电                                     |                     |    | V <sub>DS</sub> = 75 V, T <sub>C</sub> = 150°C  |                     |     | -     | 500   | μΑ   |
| I <sub>GSS</sub>                   | 栅极 - 体                                   | 漏电流                 |    | $V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$   | /                   | -   | -     | ±100  | nA   |
| 导通特性                               |  |                     |    |   |                     |     |       |       |      |
| V <sub>GS(th)</sub>                | 栅极阈值                                     | <b>直电压</b>          |    | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA   |                     | 2.5 | 3.5   | 4.5   | V    |
| R <sub>DS(on)</sub>                |  | 原极静态导通电阻            |    | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A   |                     | -   | 2.4   | 3.1   | mΩ   |
| 9 <sub>FS</sub>                    | 正向跨导                                     | ł                   |    | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A   |                     | -   | 180   | -     | S    |
| 动态特性                               |  |                     |    |   |                     |     |       |       |      |
| C <sub>iss</sub>                   | 输入电容                                     |                     |    |   |                     | -   | 11400 | 15160 | pF   |
| C <sub>oss</sub>                   | 输出电容                                     |                     |    | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1 MHz   |                     | -   | 1360  | 1810  | pF   |
| C <sub>rss</sub>                   | 反向传输                                     |                     |    |   |                     | -   | 595   | 800   | pF   |
| Q <sub>g(tot)</sub>                |  | 册极电荷总量              |    | V <sub>DS</sub> = 60 V, I <sub>D</sub> = 75 A,<br>V <sub>GS</sub> = 10 V (说明 4)                             |                     |     | 169   | 220   | nC   |
| Q <sub>gs</sub>                    |  | 极栅极电荷               |    |   |                     |     | 60    | -     | nC   |
| Q <sub>gd</sub>                    |  | 极 " 米勒 " 电荷         |    |   |                     | -   | 47    | -     | nC   |
| 开关特性                               |  |                     |    |   |                     |     |       | 1     |      |
|                                    | 导通延迟                                     | 时间                  |    |   |                     | -   | 230   | 470   | ns   |
| t <sub>r</sub>                     | 开通上升                                     |                     |    | V <sub>DD</sub> = 37.5 V, I <sub>D</sub> = 75 A,<br>R <sub>G</sub> = 25 Ω, V <sub>GS</sub> = 10 V<br>(说明 4) |                     | -   | 191   | 392   | ns   |
| t <sub>d(off)</sub>                | 关断延迟                                     |                     |    |   |                     | -   | 335   | 680   | ns   |
| t <sub>f</sub>                     |  |                     |    |   |                     | -   | 121   | 252   | ns   |
| ,<br>漏极 - 源 <b>板</b>               | 1一机合柱                                    | - <del>//+</del>    |    |   |                     |     |       |       |      |
|                                    |  |                     | 由法 |   |                     | -   | -     | 235   | А    |
| l <sub>S</sub>                     | 漏极 - 源极二极管最大正向连续电流<br>漏极 - 源极二极管最大正向脉冲电流 |                     |    |   |                     | _   | -     | 940   | A    |
| I <sub>SM</sub><br>V <sub>SD</sub> |  | 极二极官取入正问脉冲。极二极管正向电压 | 电加 | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A   |                     | _   |       | 1.3   | V    |
| <u>vs</u> D<br>t <sub>rr</sub>     |  |                     |    | $V_{GS} = 0 V, I_{SD} = 75 A,$  |                     | _   | 53    | -     | ns   |
| q <sub>rr</sub>                    | 反向恢复                                     |                     |    | $V_{GS} = 0 V, I_{SD} = 75 A,$<br>$dI_{F}/dt = 100 A/\mu s$   |                     | -   | 77    | -     | nC   |
|                                    |  |                     |    |   |                     |     |       |       |      |

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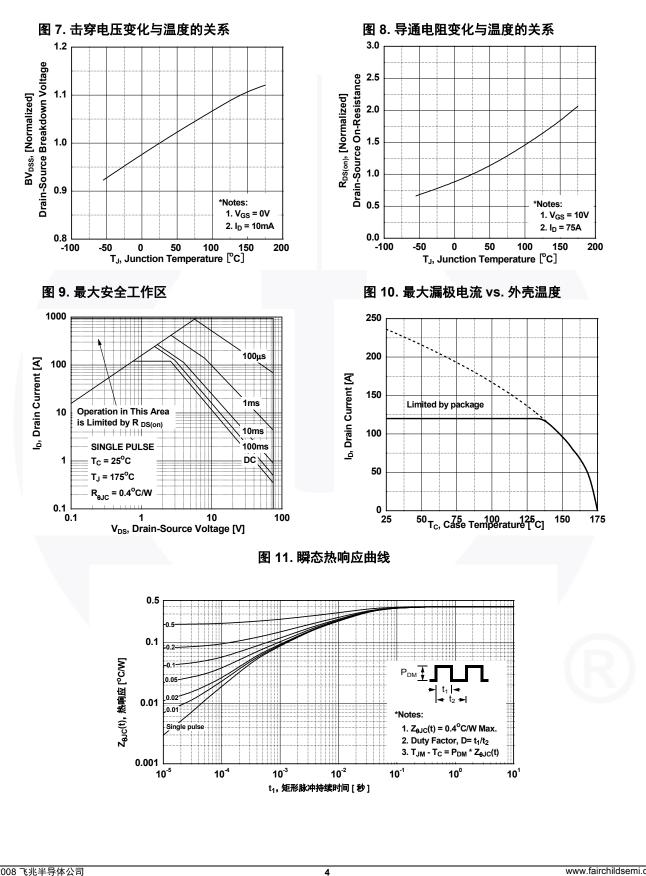
### 典型性能特征

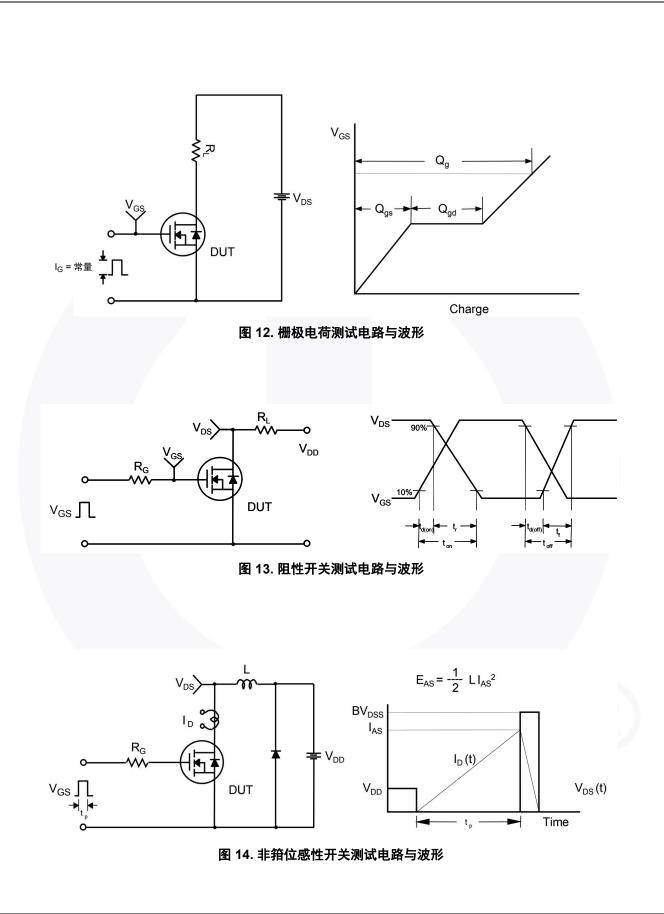


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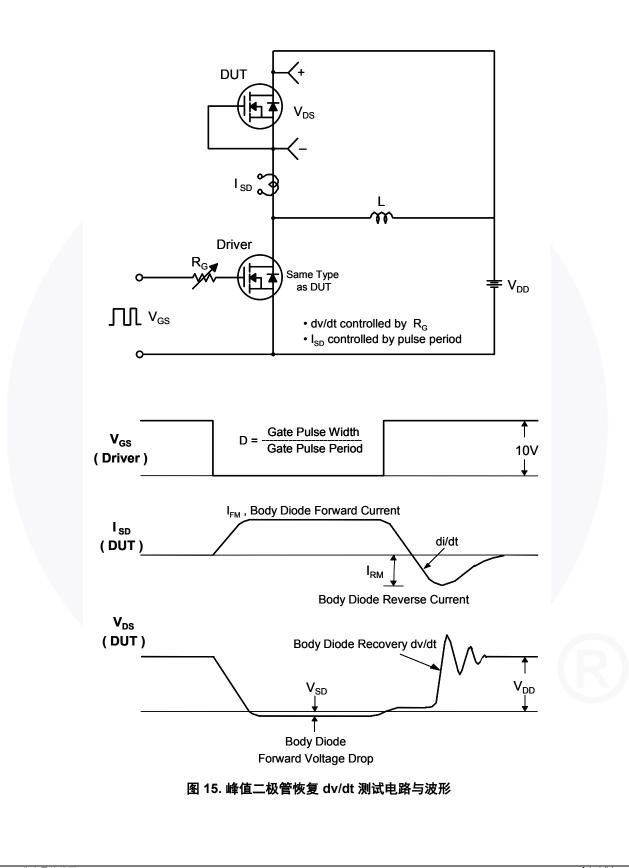
### 典型性能特征 (接上页)

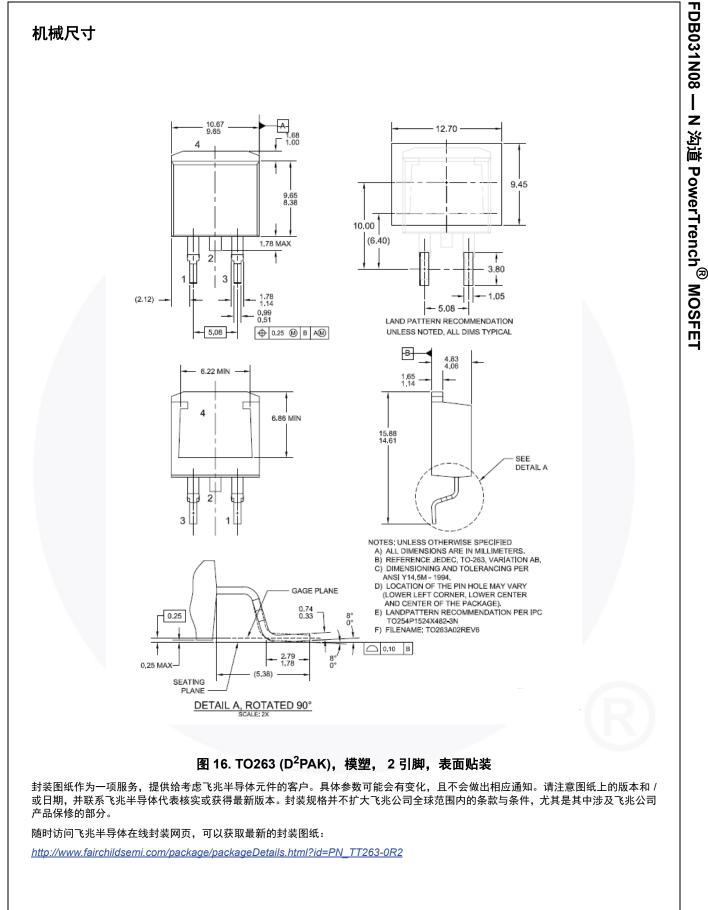




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